Fabrication of transparent conducting films composed of In\textsuperscript{3+} doped CuS and their application in flexible electroluminescent devices

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Fig. S1 EDS pattern of undoped CuS on silicon grid coated with silicon nitride.
Fig. S2 EDS of CuS films doped with 2.5 mol. % In$^{3+}$ ions on silicon grid coated with silicon nitride.
Fig. S3 Profiles of CuS films doped with (a) 0 and (b) 1% In$^{3+}$ ions (c) thickness of the films with varying concentration of In$^{3+}$ ions with dipping time 24 hours.